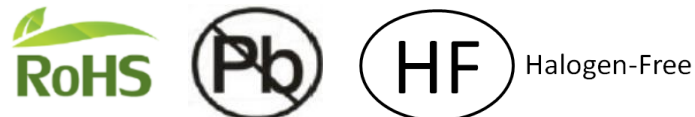


Features

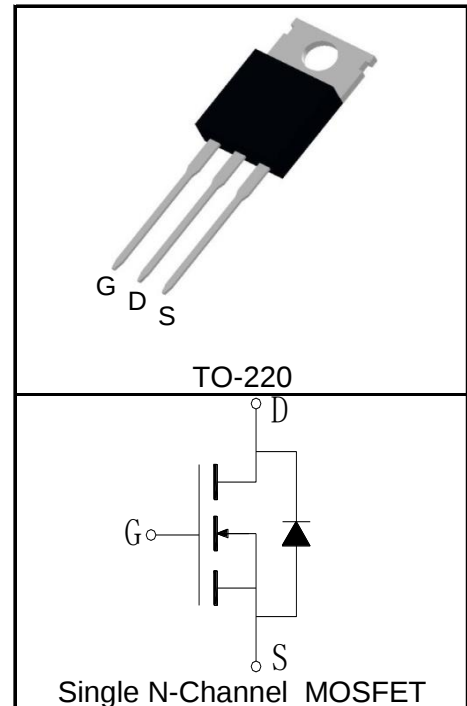
- 60V/170A,
 $R_{DS(ON)} = 2.9m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 3.8m\Omega(Typ.)@V_{GS}=4.5V$
- Excellent $Q_G \times R_{DS(on)}$ product(FOM)
- SGT Technology
- 100% Avalanche Tested

Applications

- DC-DC Converters
- High Frequency Switching and Synchronous Rectification



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	170	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _C =25°C	680	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _C =25°C	170	A
		T _C =100°C	120	
P _D	Maximum Power Dissipation	T _C =25°C	150	W
		T _C =100°C	75	
R _{θJC}	Thermal Resistance-Junction to Case		1	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		62.5	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		272	mJ

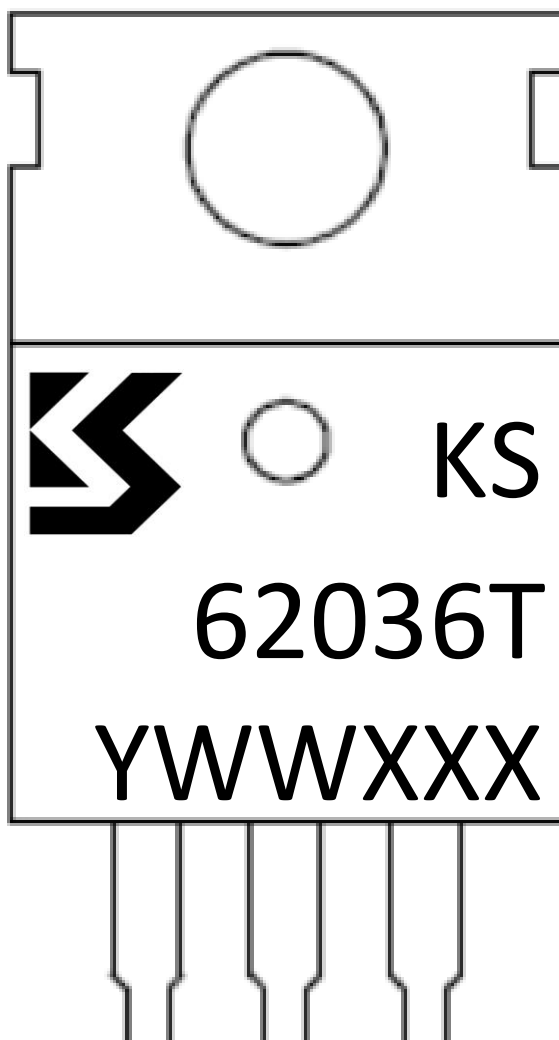
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS62036CAT			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.1	1.8	2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =30A		2.9	3.8	mΩ
		V _{GS} =4.5V, I _{DS} =20A		3.8	5	mΩ
Diode Characteristics						
V _{SD} ⑤	Diode Forward Voltage	I _{SD} =30A, V _{GS} =0V		0.83	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =30A, dI _{SD} /dt=100A/μs		55		ns
Q _{rr}	Reverse Recovery Charge			48		nC
Dynamic Characteristics ⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		0.9		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz		3355		pF
C _{oss}	Output Capacitance			1200		
C _{rss}	Reverse Transfer Capacitance			30		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, I _{DS} =30A, V _{GEN} =10V, R _G =3Ω		10		ns
t _r	Turn-on Rise Time			41		
t _{d(OFF)}	Turn-off Delay Time			31		
t _f	Turn-off Fall Time			28		
Gate Charge Characteristics ⑥						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =30A		42		nC
Q _{gs}	Gate-Source Charge			6		
Q _{gd}	Gate-Drain Charge			10		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , $I_{AS}=33A$, $L=0.5\text{mH}$, $V_{DD}=48V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

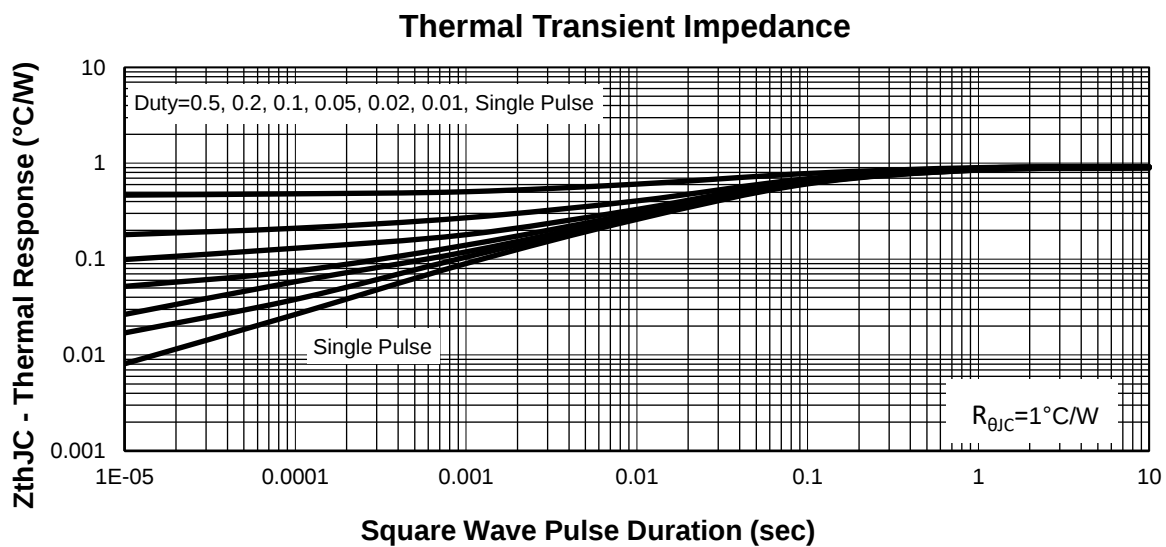
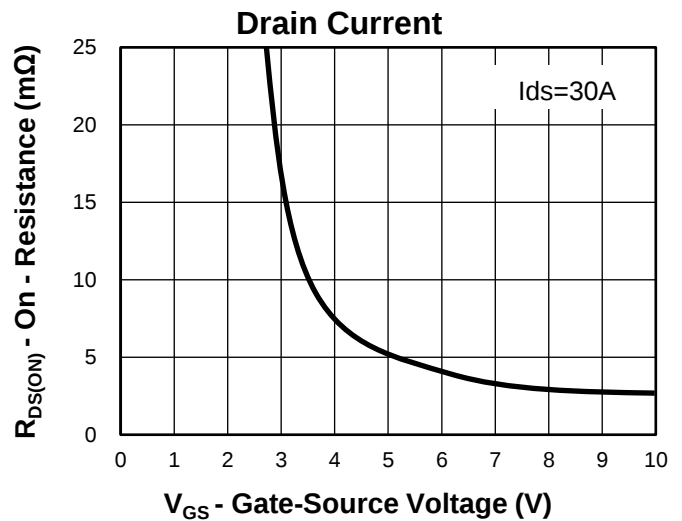
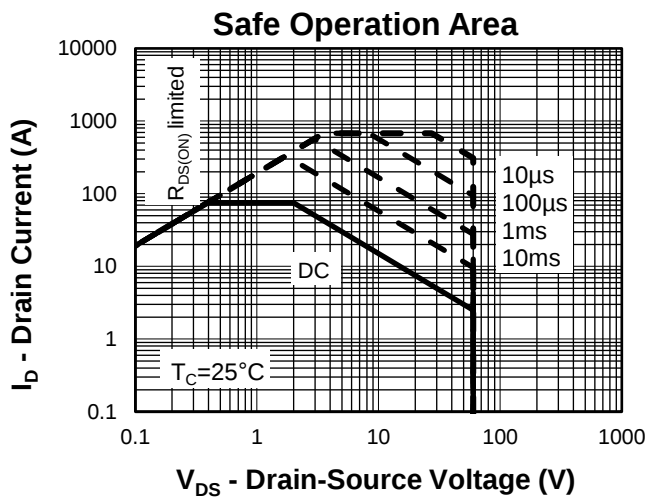
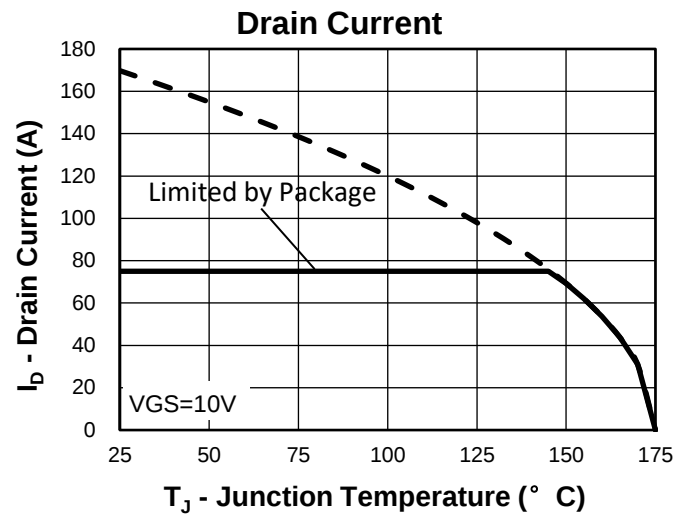
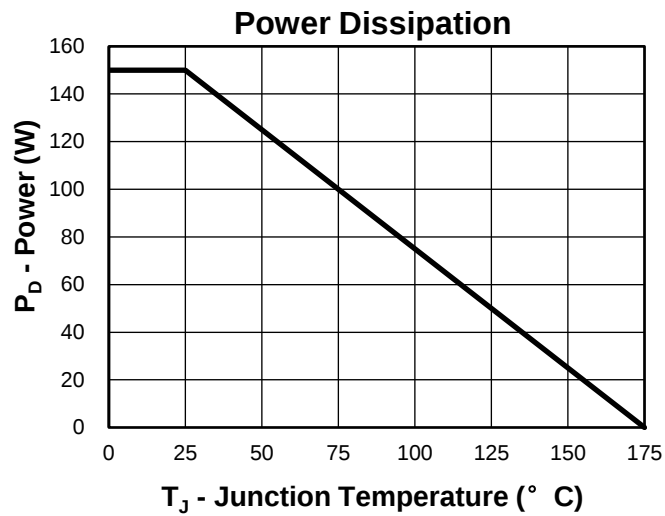
Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS62036CAT	TO-220	Tube	50	-	-

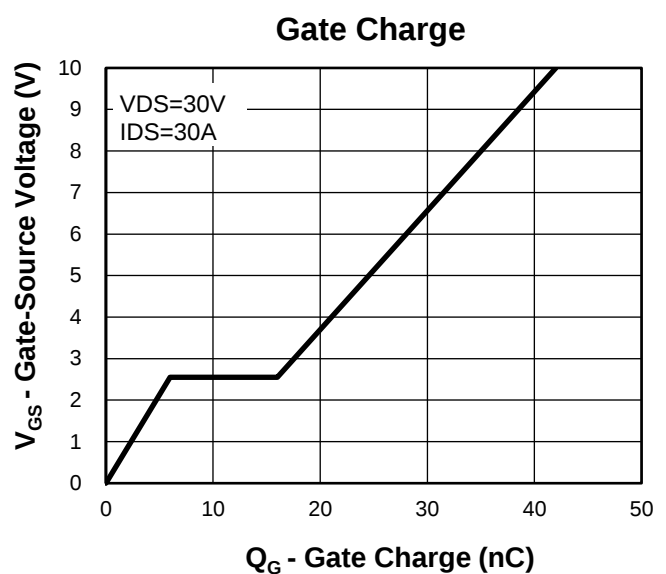
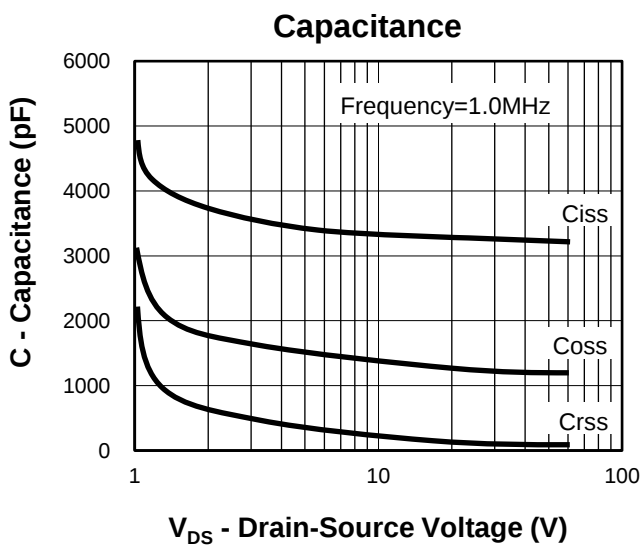
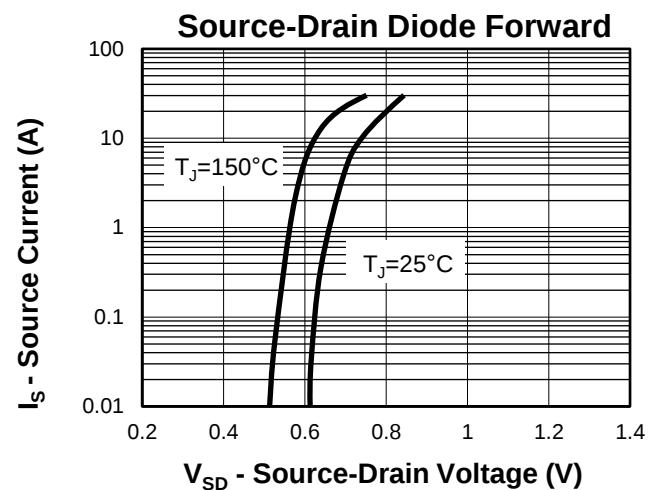
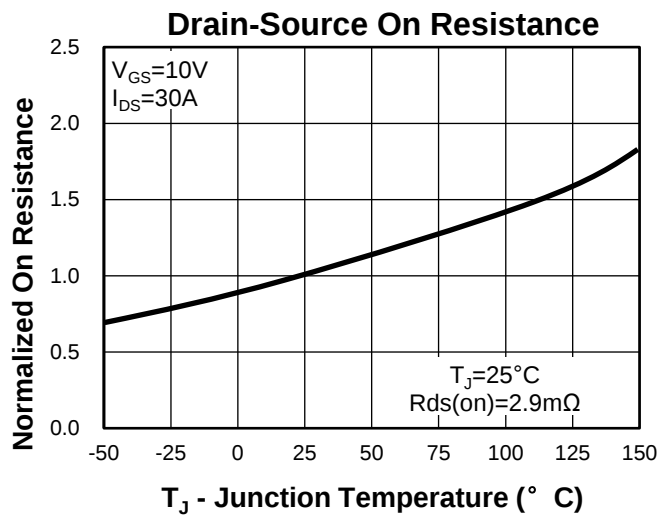
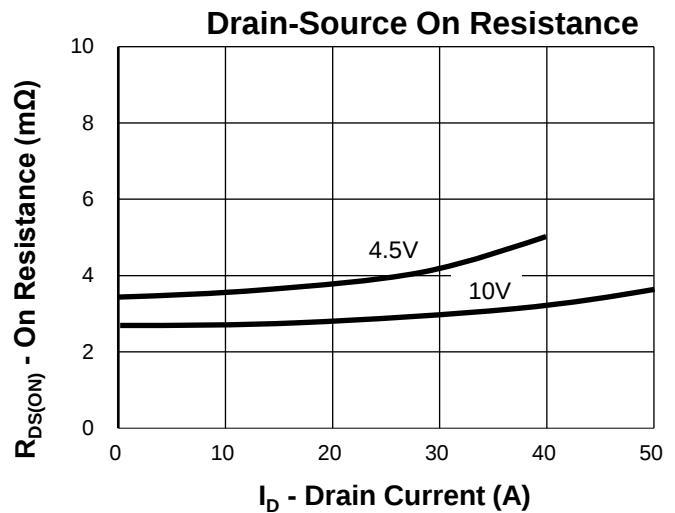
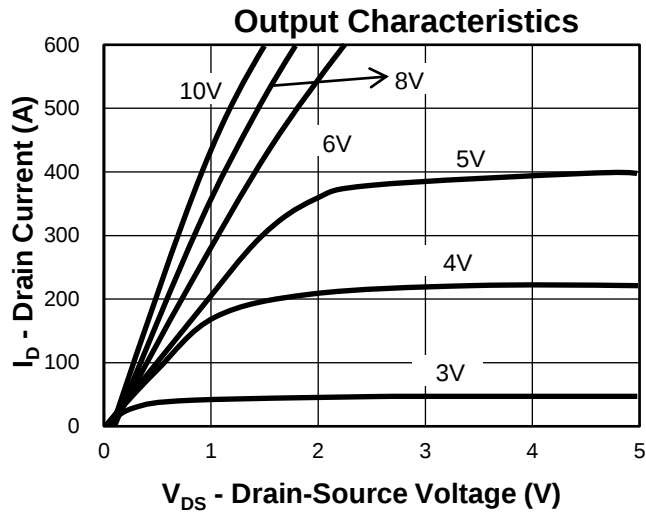


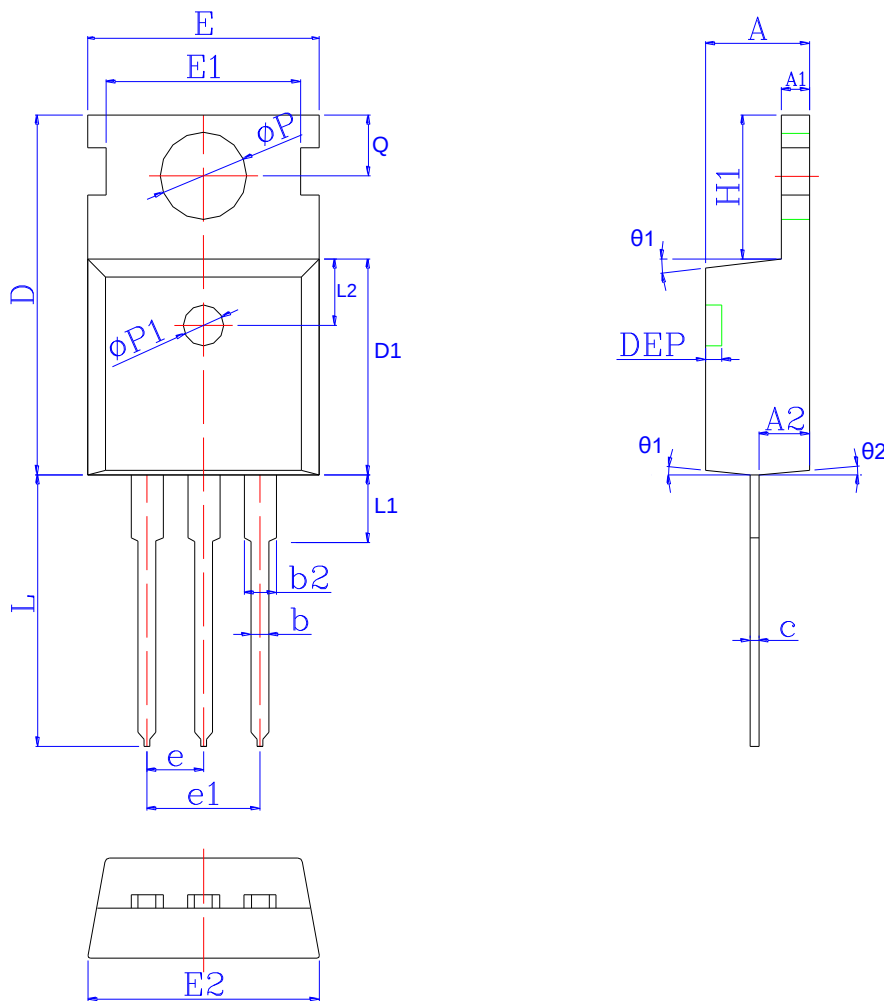
Y =Year,2017-A,2018-B,etc.
 WW =Week.
 XXX =Lot number.

Typical Characteristics



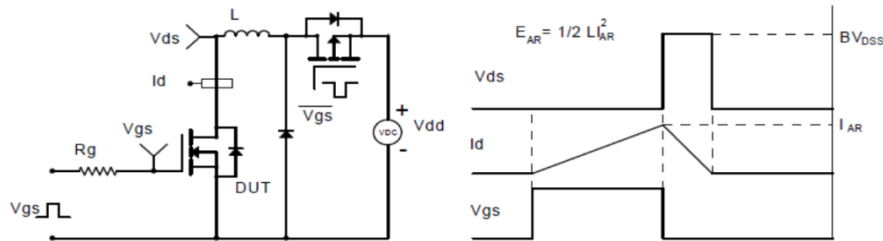
Typical Characteristics



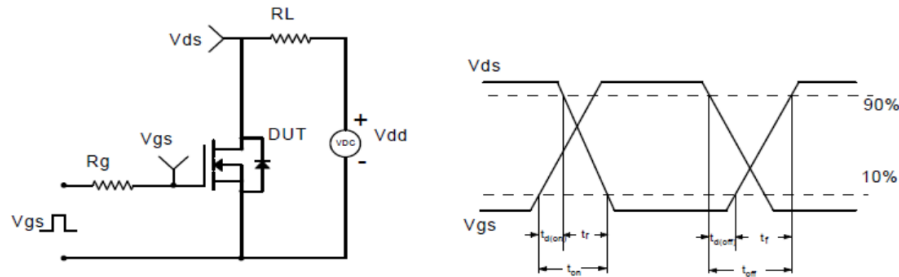
Package Information
TO-220


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.54	4.77	0.169	0.179	0.188	Φp1	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.15	1.30	1.40	0.045	0.051	0.055	e	2.54 BSC			0.10 BSC		
A2	1.90	2.25	2.60	0.075	0.089	0.102	e1	5.08 BSC			0.20 BSC		
b	0.60	0.80	1.00	0.024	0.031	0.039	H1	6.30	6.50	6.80	0.248	0.256	0.268
b2	1.17	1.28	1.72	0.046	0.050	0.068	L	12.70	13.18	13.65	0.500	0.519	0.537
c	0.40	0.50	0.60	0.016	0.020	0.024	L1	*	*	3.95	*	*	0.156
D	15.40	15.70	16.00	0.606	0.618	0.630	L2	2.50 REF			0.098 REF		
D1	8.96	9.21	9.46	0.353	0.363	0.372	Φp	3.50	3.60	3.75	0.138	0.142	0.148
DEP	*	*	0.30	*	*	0.012	Q	2.70	2.80	3.20	0.106	0.110	0.126
E	9.66	9.97	10.28	0.380	0.393	0.405	θ 1	5°	7°	9°	5°	7°	9°
E1	*	8.70	*	*	0.343	*	θ 2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.402							

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

Kwansemi Semiconductor Co.,Ltd

Email:Sales@kwansemi.com

Web:www.kwansemi.com

DISCLAIMER:

Kwansemi reserves the right to change the specifications and circuitry without notice at any time. The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.